## Vishay Siliconix



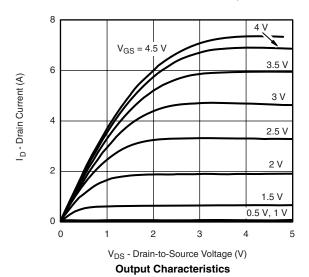
| Parameter                                     | Symbol              | Test Conditions   | Min.   | Тур.  | Max.  | Unit |
|---|---------------------|---|--------|-------|-------|------|
| Static  |                     |   |        |       |       |      |
| Gate-Threshold Voltage                        | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$   | - 0.45 |       |       | V    |
| Gate-Body Leakage                             | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$  |        |       | ± 1   | μΑ   |
| Zero Gate Voltage Drain Current               | I <sub>DSS</sub>    | V <sub>DS</sub> = - 9.6 V, V <sub>GS</sub> = 0 V  |        |       | - 1   |      |
|   |                     | V <sub>DS</sub> = - 9.6 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C  |        |       | - 5   |      |
| On-State Drain Current <sup>a</sup>           | I <sub>D(on)</sub>  | V <sub>DS</sub> - 5 V, V <sub>GS</sub> = - 4.5 V  | - 3    |       |       | Α    |
| Drain-Source On-State Resistance <sup>a</sup> | R <sub>DS(on)</sub> | V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 1 A   |        | 0.240 | 0.290 | Ω    |
|   |                     | V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 0.5 A   |        | 0.350 | 0.435 |      |
|   |                     | V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 0.3 A   |        | 0.480 | 0.580 |      |
| Forward Transconductance <sup>a</sup>         | 9 <sub>fs</sub>     | V <sub>DS</sub> = - 5 V, I <sub>D</sub> = - 1 A   |        | 3.5   |       | S    |
| Diode Forward Voltage <sup>a</sup>            | $V_{SD}$            | I <sub>S</sub> = - 1 A, V <sub>GS</sub> = 0 V   |        |       | - 1.2 | V    |
| Dynamic <sup>b</sup>                          |                     |   |        |       |       |      |
| Total Gate Charge                             | $Q_g$               | V <sub>DS</sub> = -6 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -1 A   |        | 3.2   | 5     | nC   |
| Gate-Source Charge                            | $Q_{gs}$            |   |        | 0.69  |       |      |
| Gate-Drain Charge                             | $Q_{gd}$            |   |        | 0.61  |       |      |
| Turn-On Delay Time                            | t <sub>d(on)</sub>  | $V_{DD}$ = - 6 V, $R_L$ = 6 Ω $I_D$ $\cong$ - 1 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 6 Ω $I_F$ = - 1 A, $dI/dt$ = 100 A/ $\mu$ s |        | 210   | 340   | ns   |
| Rise Time                                     | t <sub>r</sub>      |   |        | 450   | 720   |      |
| Turn-Off Delay Time                           | t <sub>d(off)</sub> |   |        | 910   | 1550  |      |
| Fall Time                                     | t <sub>f</sub>      |   |        | 1000  | 1600  |      |
| Source-Drain Reverse Recovery Time            | t <sub>rr</sub>     |   |        | 540   | 860   |      |

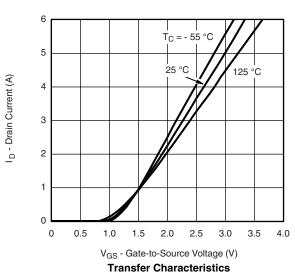
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

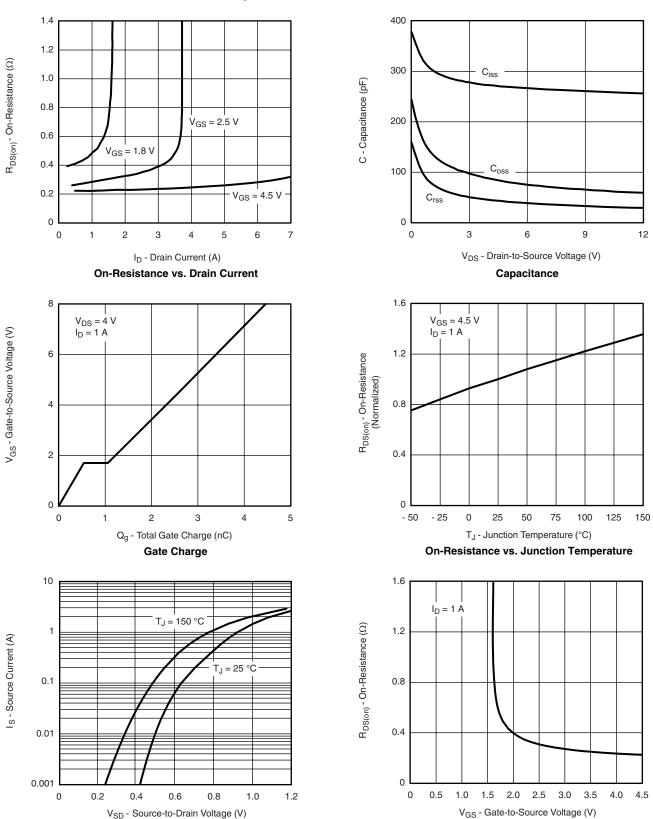








### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



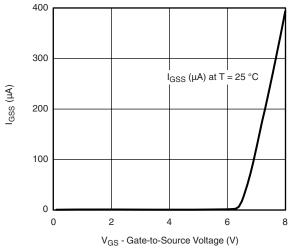
Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-Source Voltage

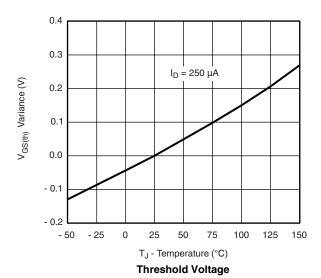
# Vishay Siliconix

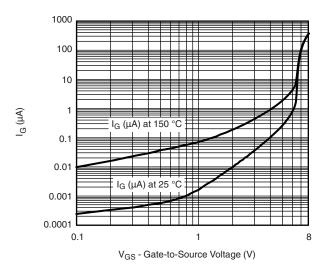
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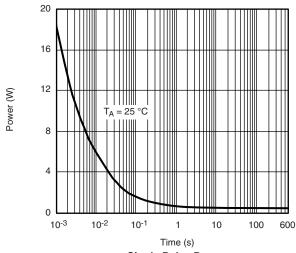


#### Gate-Current vs. Gate-to-Source Voltage



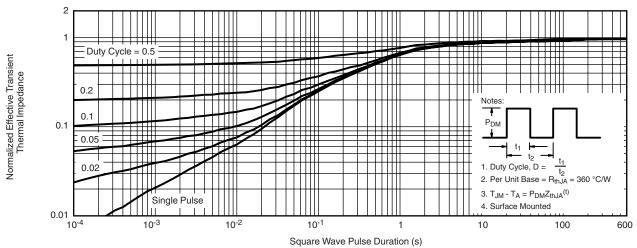


Gate-to-Source Voltage vs. Gate Current

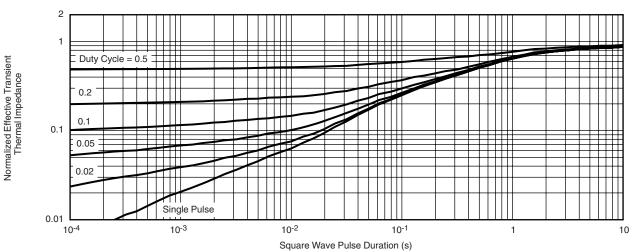




#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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